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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("6348705").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM TDB	OR	OFF	2004/11/24 12:23
L2	1	"6180482".PN.	USPAT; USOCR	OR	ON	2004/11/24 12:23
L3	24	@ad<="20010508" and 'amorphous BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:27
L4	9	@ad<="20010508" and 'amorphous SBT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:24
L5		@ad<="20010508" and 'amorphous' with 'BST' and 'capacitance density' and 'current leakage'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/11/24 12:28
L6	5	@ad<="20010508" and 'amorphous' and 'capacitance density' and 'current leakage'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:43
L7	1	@ad<="20010508" and 'amorphous' with 'SBT' and 'capacitance density' and 'current leakage'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:29
L8	0	@ad<="20010508" and 'capacitor' and "'IrO.sub.2" same "'IrO.sub.3" same 'Ir'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:45
L9	0	@ad<="20010508" and 'capacitor' and "IrO.sub.2"" same "'IrO.sub.3""	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:45
L10	571	@ad<="20010508" and 'capacitor' and "IrO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:45
	2	@ad<="20010508" and 'capacitor' and "Ir.sub.2O.sub.3"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB			2004/11/24 12:45

L12	5692	(((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.) and @ad<="19991222"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:51
S1	2	("6348705").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/16 08:11
S2	13687	@ad<="20010508" and 'high dielectric constant'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 08:31
S3	132	(@ad<="20010508" and 'high dielectric constant') and 'conductive barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:24
S4	119	((@ad<="20010508" and 'high dielectric constant') and 'conductive barrier') and Al	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 08:24
S 5	77	((@ad<="20010508" and 'high dielectric constant') and 'conductive barrier') and Aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2002/09/16 08:25
S6	3291	@ad<="20010508" and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 08:33
S7	79	(@ad<="20010508" and 'BST') and 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2003/01/29 13:41
S8	39	((@ad<="20010508" and 'BST') and 'TiAIN') and aluminum	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 06:54
S9	6626	((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/16 11:37

						15.48
S10	24	(((257/295-296) or (257/751) or (257/310) or (438/3) or (257/763-764) or (257/303) or (257/306)).CCLS.) and @ad<="20010508" and 'BST' and 'TiAIN' and 'metal layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:51
S11	29173	@ad<="20010508" and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 12:05
S12	30	(@ad<="20010508" and 'ferroelectric') and 'BST' and 'TiAIN' and 'metal layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/30 07:15
S13	29	(@ad<="20010508" and 'ferroelectric') and 'BST' and 'TiAIN' and 'aluminum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	©R.	ON	2002/09/16 13:26
S14	20	(@ad<="20010508" and 'ferroelectric') and 'capacitor' with 'BST' and 'TiAlN' and 'aluminum'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 13:26
S15	25	@ad<="20010508" and 'perovskite BST' or 'amorphous BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 15:09
S16	3	@ad<="20010508" and 'amorphous BST' and conductive adj barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/24 12:24
S17	569	(257/310).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/09/16 15:41
S18	532	((257/310).CCLS.) and @ad<="20010508"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 13:56
S19	11	(@ad<="20010508" and 'ferroelectric') and 'BST' and 'barrier' and 'aluminum layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/09/16 15:45

S20	. 270	@ad<="19991222" and 'conductive barrier' and 'TiN'	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2003/05/12 12:52
S21	566	((257/310).CCLS.) and @ad<="20010508"	IBM_TDB US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	⊕R	ON	2003/01/29 14:05
S22	43	@ad<="19991222" and 'conductive barrier' and 'TiN' and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:05
S23	6	@ad<="19991222" and 'conductive barrier' and 'TiN' and 'BST' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 15:02
S24	2342	@ad<="19991222" and (257/295-296).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:15
S25	795	@ad<="19991222" and (257/751). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2003/01/29 14:09
S26	1232	@ad<="19991222" and (257/763-764).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:10
S27	372	@ad<="19991222" and (257/303). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2003/01/29 14:11
S28	1094	@ad<="19991222" and (257/306). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:12
S29	479	@ad<="19991222" and (438/3). ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	ΘR	ON	2003/01/29 14:12
S 30	1072	@ad<="19991222" and (438/439-440).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/29 14:13

S 31	687	@ad<="19991222" and (438/687-688).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2003/01/29 14:21
S32	4	(("6294420") or ("6365517")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2003/01/29 14:21
S33	38	@ad<="19991222" and 'high dielectric constant' and 'conductive	DERWENT; IBM_TDB US-PGPUB; USPAT;	OR	ON	2003/01/29 14:26
S34	21	barrier' and 'copper' @ad<="19991222" and	EPO; JPO; DERWENT; IBM_TDB US-PGPUB;	OR	ON	2003/01/29 15:02
		'conductive barrier' and 'TiN' and 'BST' and 'aluminum'	USPAT; EPO; JPO; DERWENT; IBM_TDB			
S 35	29	@ad<="19991222" and 'ferroelectric' and 'TiAIN' and 'metal layer'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 08:54
S36	8	@ad<="19991222" and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2003/05/12 14:27
S37	17	@ad<="19991222" and 'conductive barrier' and 'TiAIN'	IBM_TDB US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 12:52
S38	5	@ad<="19991222" and 'BST' and 'conductive barrier' with 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2003/05/12 13:00
S 39	10	@ad<="19991222" and 'copper' and 'TiAIN' and 'BST'	IBM_TDB US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:42
S40	1	@ad<="19991222" and 'copper' same 'TiAIN' same 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 13:07
S41	0	@ad<="19991222" and 'capacitor' with 'BST' with 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:25

S42	2	@ad<="19991222" and 'BST' with 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:25
S43	8	@ad<="19991222" and 'capacitor' with 'ferroelectric' with 'conductive diffusion barrier'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/07/01 07:04
S44	0	@ad<="19991222" and copper near electrode and 'BST' same 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:39
S45	3	@ad<="19991222" and copper and 'BST' same 'TiAIN'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:39
S46	50	@ad<="19991222" and 'Al' and 'TiAIN' and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:46
S47	25	@ad<="19991222" and 'Aluminum' and 'TiAIN' and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 08:25
S48	48	@ad<="19991222" and 'conductive' and 'TiAIN' and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/05/12 14:58
S49	15	@ad<="19991222" and 'stack capacitor' and 'TiAIN' and 'BST'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/07/01 07:22
S 50	2	"20020167086"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/15 12:55
S51	8	@ad<="20010508" and 'BST' same 'TiN' same 'aluminum' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:02
S52	3	@ad<="20010508" and 'high k' same 'TiN' same 'aluminum' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:03

S53	2	("5990541").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/07/01 07:03
S54	5	@ad<="19991222" and 'ferroelectric' same 'barrier' same 'copper' with 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/07/01 07:08
S55	236	@ad<="19991222" and 'ferroelectric' same 'barrier' same 'metal' with 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:13
S56	4	@ad<="19991222" and 'capacitor' same 'ferroelectric' same 'barrier' same 'copper' with 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:09
\$57	5	@ad<="19991222" and 'stack capacitor' and 'TiAIN' and 'PZT' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:22
S58	31	@ad<="19991222" and 'stack capacitor' and 'TiN' and 'PZT' and 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:29
S 59	2	@ad<="19991222" and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:33
S60	3	@ad<="20010508" and 'capacitor' and 'TiN' and 'PZT' and 'copper electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:34
S61	283	@ad<="20010508" and 'capacitor' and 'TiN' and 'PZT' and 'al' with 'electrode'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:35
S62	77	@ad<=''20010508" and 'capacitor' same 'electrode' with 'aluminum' same 'barrier' and 'PZT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 07:40
S63	· 15	@ad<="20010508" and 'capacitor' same 'electrode' with 'copper' same 'barrier' and 'PZT'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 08:15

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S	64	3 .	@ad<="20010508" and 'electrode' with 'conductive barrier' with 'PZT'	US-PGPUB; USPAT;	OR	ON	2004/07/01 08:19
			-	EPO; JPO;			
			·	DERWENT; IBM_TDB			
S	65	55	@ad<="20010508" and 'electrode'	US-PGPUB;	OR	ON	2004/07/01 08:32
			with 'TiN' with 'PZT'	USPAT; EPO: JPO:			
				DERWENT;			
	cc	04		IBM_TDB	00	ON	0004/07/04 00:00
)	66	81	@ad<="20010508" and 'electrode' adj2 'copper' with 'TiN'	US-PGPUB; USPAT;	OR	ON	2004/07/01 08:33
				EPO; JPO; DERWENT;		-	
				IBM_TDB			
s	67	5	@ad<="20010508" and 'copper'	US-PGPUB;	OR	ON	2004/07/01 08:45
			with 'electrode' with 'TiN' and 'BST'	USPAT; EPO; JPO;			
				DERWENT; IBM TDB			
S	68	3	@ad<="20010508" and 'copper'	US-PGPUB;	OR	ON	2004/07/01 08:45
		_	with 'electrode' with 'TiN' and 'high	USPAT;			
			K .	EPO; JPO; DERWENT;			
				IBM_TDB		:::: <u>:</u> :::::::::::::::::::::::::::::::	
S	69	66	@ad<="20010508" and 'copper' with 'electrode' with 'TiN' and 'high	US-PGPUB; USPAT:	OR	ON	2004/07/01 08:48
1 0 v v 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	* * * * * * * * * * * * * * * * * * *		dielectric'	EPO; JPO;			
				DERWENT; IBM_TDB			
S	70	3	@ad<="20010508" and 'copper'	US-PGPUB;	OR	ON	2004/07/01 08:49
	:		adj2 'electrode' with 'TiN' and 'high dielectric'	USPAT; EPO; JPO;			
				DERWENT; IBM_TDB			
S	71	25	@ad<="19991222" and	US-PGPUB;	OR	ON	2004/07/01 11:41
			'ferroelectric' with 'capacitor' and	USPAT;			
			'TiAlN' and 'metal layer'	EPO; JPO; DERWENT;			
	-	_		IBM_TDB	00		0004/07/04 00 00
S	72	0	@ad<="19991222" and 'ferroelectric' with 'capacitor' and	US-PGPUB; USPAT;	OR	ON	2004/07/01 09:02
			'TiAIN' and 'copper electrode'	EPO; JPO; DERWENT;			
				IBM_TDB			
S	73	1	"5053917".PN.	USPAT	OR	OFF	2004/07/01 10:37
S	74	0	@ad<="19991222" and 'copper' same "'IrO.sub.2'" same "'Ir.sub.O.	US-PGPUB; USPAT;	OR	ON	2004/07/01 11:43
			sub3" same 'Ir' and 'ferroelectric'	EPO; JPO;		,	
			·	DERWENT; IBM TDB		, ,	
S	75	4	@ad<="19991222" and 'copper	US-PGPUB;	OR	ON	2004/07/01 11:43
			same "'IrO.sub.2" same 'Ir' and 'ferroelectric'	USPAT; EPO; JPO;			
				DERWENT;			
			4/04 12·54·47 PM Page 8	IBM_TDB			

S76	2	@ay<="1999" and tang-shaoping. in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/01 14:38
S77	6	@ay<="1999" and summerfelt-scott.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 08:38
S78	4	@ay<="1999" and crenshaw-darius.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 08:38
S79	1	@ay<="1999" and kirlin-peter.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/07/02 08:41
S80	5	@ay<="1999" and gnade-bruce.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 08:44
S81	31	@ay<="1999" and gilbert.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:08
S82		@ay<="1999" and xing-guoqiang. in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 10:59
S83	692	@ay<="1999" and 'capacitor' same 'lower electrode' with 'polysilicon'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:18
S84	1	@ay<="1999" and 'capacitor' same 'lower electrode' with 'polysilicon' same 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:19
S85	9	@ay<="1999" and 'capacitor' same 'plug' with 'silicon' same 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:24
S86	29	@ay<="1999" and 'contact plug' with 'silicon' same 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:25

S87	21	@ay<="1999" and 'contact plug' with 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:37
S88	48	@ay<="1999" and 'capacitor' and 'doped' adj1 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:38
S89	76	@ay<="1999" and 'electrode' and 'doped' adj1 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:38
S90	17	@ay<="1999" and 'capacitor' with 'electrode' and 'doped' adj1 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/07/02 09:51
S91	33	@ay<="1999" and 'electrode' same 'doped' adj1 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 09:53
S92	7	@ay<="1999" and 'capacitor' with 'electrode' same 'doped' adj1 'silicon' with 'copper'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON Î	2004/07/02 09:52
S93	0	@ay<="1999" and ma-shawing.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 11:00
S94	9	@ay<="1999" and ma-shawing.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 11:00
S95	0	ma-shawing.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ,	ON	2004/07/02 11:00
S96	1	@ay<="1999" and ma-shawming. in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 11:01
S97	9	ma-shawming.in. and 'ferroelectric'	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/02 11:01

S98	18	@ad<="20010508" and 'amorphous BST' and 'perovskite'	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON	2004/07/02 13:07
		·	IBM_TDB			